



# 3DD11

## NPN Silicon Low Frequency High Power Transistor



### Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: General, GS

### TECHNICAL DATA:

( $T_a = 25^\circ\text{C}$ )

Parameter name	Symbols	Unit	Specifications									Test Condition
			A	B	C	D	E	F	G	H	I	
Collector-Emitter Voltage	$V_{CEO}$	V	50	100	150	200	250	300	400	500	600	
Emitter-Base Voltage	$V_{EBO}$	V	5									
Max. Collector Current	$I_{CM}$	A	A~F:30, G~I:15									
Max. Collector Dissipation	$P_{CM}$	W	300									$T_c:75^\circ\text{C}$
Junction Temperature	$T_{jm}$	$^\circ\text{C}$	175									
Storage Temperature	$T_{stg}$	$^\circ\text{C}$	-55~+175									
Collector-Emitter Leakage Current	$I_{CEO}$	mA	Max.:5.0									A: $V_{CE}=30\text{V}$ ;B: $V_{CE}=50\text{V}$ ; C~I: $V_{CE}=100\text{V}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:2.0									A~F: $I_C=15\text{A}$ , $I_B=1.5\text{A}$
												G~I: $I_C=7.5\text{A}$ , $I_B=1.5\text{A}$
DC Current Gain	$h_{FE}$		Max.:120					Min.:15				A~F: $V_{CE}=5\text{V}$ , $I_C=15\text{A}$
			Max.:120					Min.: 7				G~I: $V_{CE}=10\text{V}$ , $I_C=7.5\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	A	B	C	D	E	F	G	H	I	$I_C=5\text{mA}$
			50	100	150	200	250	300	400	500	600	
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	5									$I_E=15\text{mA}$

### $h_{FE}$ Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue
$h_{FE}$	7~15	15~25	25~40	40~55	55~80	80~120

### Outline and Dimensions: